

CentralTM Semiconductor Corp.

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Manufacturers of World Class Discrete Semiconductors

MPQ2907A

PNP SILICON QUAD TRANSISTOR

JEDEC TO-116 CASE

DESCRIPTION

The CENTRAL SEMICONDUCTOR MPQ2907A type is comprised of four independent Silicon PNP Transistors mounted in a 14 PIN DIP, designed for general purpose amplifier and switching applications.

MAXIMUM RATINGS (T_A=25°C)

	SYMBOL		UNITS
Collector-Base Voltage	V _{CB0}	60	V
Collector-Emitter Voltage	V _{CEO}	60	V
Emitter-Base Voltage	V _{EBO}	5.0	V
Collector Current	I _C	600	mA
Power Dissipation (Each Transistor)	P _D	650	mW
Power Dissipation (Total Package)	P _D	1.9	W
Operating and Storage Junction Temperature	T _J , T _{stg}	-65 to +150	°C

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I _{CBO}	V _{CB} =30V			50	nA
I _{EBO}	V _{CE} =3.0V			50	nA
BV _{CEO}	I _C =10mA	60			V
BV _{CBO}	I _C =10uA,	60			V
BV _{EBO}	I _E =10uA	5.0			V
V _{CE(SAT)}	I _C =150mA, I _B =15mA			0.4	V
V _{CE(SAT)}	I _C =300mA, I _B =30mA			1.6	V
V _{BE(SAT)}	I _C =150mA, I _B =15mA			1.3	V
V _{BE(SAT)}	I _C =300mA, I _B =30mA			2.6	V
h _{FE}	V _{CE} =10V, I _C =10mA	75			
h _{FE}	V _{CE} =10V, I _C =150mA	100			
h _{FE}	V _{CE} =10V, I _C =300mA	50			
f _T	V _{CE} =20V, I _C =50mA, f=100MHz	200			MHz
C _{ib}	V _{BE} =2.0V, I _C =0, f=1.0kHz		6.0	8.0	pF
C _{ob}	V _{CB} =10V, I _E =0, f=1.0kHz		20	30	pF
t _{on}	V _{CC} =30V, I _C =150mA, I _{B1} =15mA		30		ns
t _{off}	V _{CC} =30V, I _C =150mA, I _{B1} =I _{B2} =15mA		150		ns